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Hyperfast Rectifier, 15 A FRED Pt[®] G5



PRIMARY CHARACTERISTICS								
I _{F(AV)}	15 A							
V _R	1200 V							
V _F at I _F at 125 °C	1.7 V							
t _{rr}	37 ns							
T _J max.	175 °C							
Package	D ² PAK 2L (TO-263AB 2L)							
Circuit configuration	Single							

FEATURES

- Hyperfast and optimized Qrr
- Best in class forward voltage drop and switching
 losses trade off
 Compliant
 HALOGEN
 HALOGEN
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- · Polyimide passivation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant.

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		1200	V						
Average rectified forward current	I _{F(AV)}	T _C = 110 °C, D = 0.50	15							
Repetitive peak forward current	I _{FRM}	T _C = 110 °C, D = 0.50, f = 20 kHz	30	А						
Non-repetitive peak surge current	I _{FSM}	$T_C = 45 \text{ °C}, t_p = 10 \text{ ms}, \text{ sine wave}$	125							
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	1200	-	-					
Forward voltage	V _F	I _F = 15 A	-	1.9	2.5	V				
		I _F = 15 A, T _J = 125 °C	-	1.7	-					
Reverse leakage current	I _R	$V_{R} = V_{R}$ rated	-	-	50					
neverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA				
Junction capacitance	CT	V _R = 200 V	-	10	-	pF				
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH				



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_{\rm F} = 1.0 \rm A, dI_{\rm F}/c$	$t = 100 \text{ A/}\mu\text{s}, \text{V}_{\text{R}} = 30 \text{ V}$	-	37	-				
Reverse recovery time	t _{rr}	T _J = 25 °C		-	95	-	ns			
		T _J = 125 °C		-	146	-	115			
Peak recovery current		T _J = 25 °C	I _F = 10 A dI _F /dt = 600 A/μs	-	14	-	A			
	I _{RRM}	T _J = 125 °C	$V_{\rm R} = 400 \text{ V}$	-	19	-				
Reverse recovery charge	0	T _J = 25 °C		-	545	-	nC			
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1200	-				
		T _J = 25 °C		-	75.5	-	ns			
Reverse recovery time	t _{rr}	T _J = 125 °C		-	100	-				
Book recovery ourrept		T _J = 25 °C	I _F = 15 A dI _F /dt = 1000 A/μs	-	23	-	A			
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm R} = 800 \text{ V}$	-	35	-				
	0	T _J = 25 °C		-	935	-				
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1985	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.7	°C/W				
Weight			-	2.0	-	g				
weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Marking device		Case style D ² PAK 2L (TO-263AB 2L)		E5TH1	1512SH					

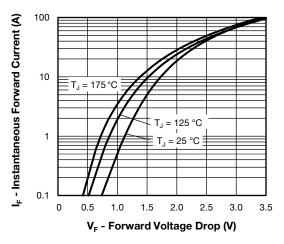


Fig. 1 - Forward Voltage Drop Characteristics

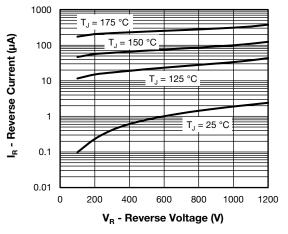


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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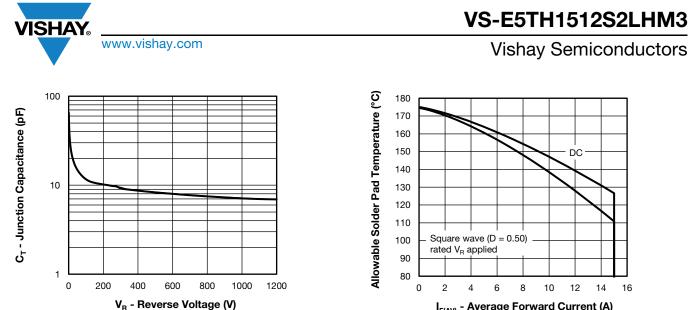


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

14 16 I_{F(AV)} - Average Forward Current (A)

Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

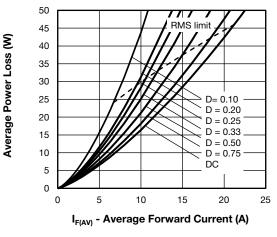


Fig. 5 - Forward Power Loss Characteristics

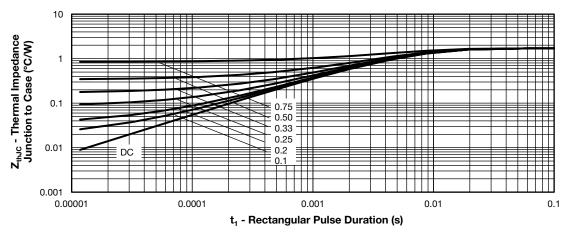


Fig. 6 - Transient Thermal Impedance, Junction to Case

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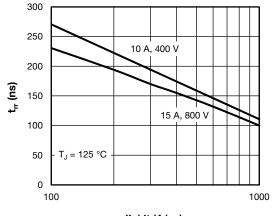
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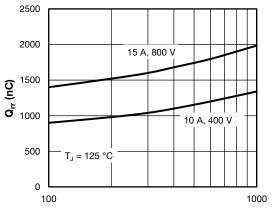
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dl_F/dt (A/µs)

Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt



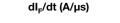


Fig. 8 - Typical Stored Charge vs. dl_F/dt

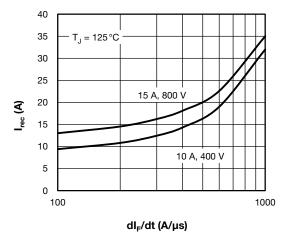


Fig. 9 - Typical Stored Charge vs. dl_F/dt



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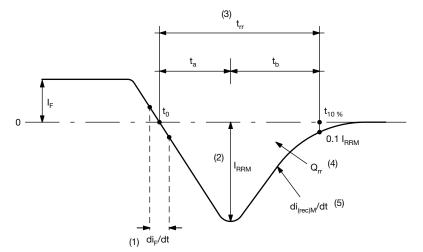


Fig. 10 - Reverse Recovery Waveform and Definitions

Notes

- $^{(1)}$ di_F/dt rate of change of current through zero crossing
- $^{(2)}\ \ I_{RRM}$ peak reverse recovery current
- $^{(3)}$ t_{rr} reverse recovery time measured from t₀, crossing point of negative going I_F, to point t_{10%}, 0.1 I_{RRM}
- $^{(4)}$ Q_{rr} area under curve defined by t_0 and $t_{10\ \%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE

Device code	VS-	Е	5	т	н	15	12	S2	L	н	М3
		2	3	4	5	6	7	8	9	(10)	(11)
	1 -	· Visl	hay Sem	nicondu	ctors pr	oduct					
	2 -	• E=	single o	liode							
	3 -	- 5 =	FRED g	eneratio	on 5						
	4 -		kage:								
			TO-263			ige					
	5 -		hyperfa		-						
	6 -	· Cui	rent rati	ng (15 =	= 15 A)						
	7 -	Vol	tage rati	ng (12 =	= 1200 \	/)					
	8 -	· S2	= true 2	pin D ² F	PAK						
	9 -	· No	ne = tub	e (50 pi	eces)						
		۰L	= tape a	and reel	(left ori	ented, f	or D ² PA	AK pack	age)		
		If needed different orientation/packaging, please contact factory									
	10 - H = AEC-Q101 qualified										
	11 -	11 - Environmental digit:									
		M3	= halog	en-free,	RoHS-	complia	ant, and	termina	ation lea	ld (Pb)-1	free

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ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-E5TH1512S2LHM3	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96683					
Part marking information	www.vishay.com/doc?96693					
Packaging information	www.vishay.com/doc?95032					

Outline Dimensions

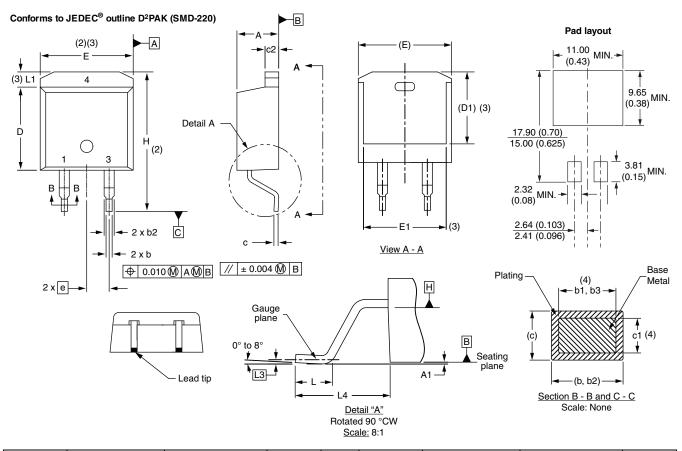


2L-D²PAK

DIMENSIONS in millimeters and inches

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SYMBOL	MILLIM	ETERS	INC	HES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.			STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L3	0.25	BSC	0.010	BSC	
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2							

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 ⁽²⁾ The outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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